

Triacs

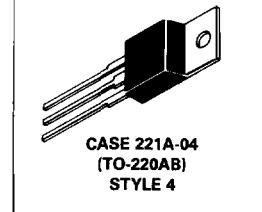
Silicon Bidirectional Triode Thyristors

. . . designed primarily for industrial and consumer applications for full wave control of ac loads such as appliance controls, heater controls, motor controls, and other power switching applications.

- Sensitive Gate Triggering in 3 Modes for AC Triggering on Sinking Current Sources (MAC228 Series)
- Four Mode Triggering for Drive Circuits that Source Current (MAC228A Series)
- All Diffused and Glass-Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal resistance and High Heat Dissipation
- Center Gate Geometry for Uniform Current Spreading

**MAC228
Series
MAC228A
Series**

**TRIACS
8 AMPERES RMS
200 thru 800 VOLTS**



3

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage, Note 1 ($T_J = -40$ to 110°C 1/2 Sine Wave 50 to 60 Hz, Gate Open)	V_{DRM}		Volts
<i>MAC228-4, MAC228A4</i> <i>MAC228-6, MAC228A6</i> <i>MAC228-8, MAC228A8</i> <i>MAC228-10, MAC228A10</i>		200 400 600 800	
On-State RMS Current ($T_C = 80^\circ\text{C}$) Full Cycle Sine Wave 50 to 60 Hz	$I_{T(\text{RMS})}$	8	Amps
Peak Non-Repetitive Surge Current (One Full Cycle 60 Hz, $T_J = 110^\circ\text{C}$)	I_{TSM}	80	Amps
Circuit Fusing ($t = 8.3$ ms)	I^2t	26	A^2s
Peak Gate Current ($t \leq 2 \mu\text{s}$)	I_{GM}	± 2	Amps
Peak Gate Voltage ($t \leq 2 \mu\text{s}$)	V_{GM}	± 10	Volts
Peak Gate Power ($t \leq 2 \mu\text{s}$)	PGM	20	Watts

Note 1. V_{DRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded. (continued)

Devices listed in bold, italic are Motorola preferred devices.

MAC228 Series • MAC228A Series

MAXIMUM RATINGS — continued

Rating	Symbol	Value	Unit
Average Gate Power ($T_C = 80^\circ\text{C}$, $t \leq 8.3 \text{ ms}$)	$P_{G(\text{AV})}$	0.5	Watts
Operating Junction Temperature Range	T_J	-40 to 110	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to 150	$^\circ\text{C}$
Mounting Torque		8	in. lb.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta\text{JC}}$	2.2	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient	$R_{\theta\text{JA}}$	60	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ and either polarity of MT2 to MT1 voltage unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Blocking Current ($V_D = \text{Rated } V_{\text{DRM}}$) $T_J = 25^\circ\text{C}$ $T_J = 110^\circ\text{C}$	I_{DRM}	—	—	10 2	μA mA
Peak On-State Voltage ($ I_{\text{TM}} = 11 \text{ A Peak, Pulse Width} \leq 2 \text{ ms, Duty Cycle} \leq 2\%$)	V_{TM}	—	—	1.8	Volts
Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ V}$, $R_L = 100 \Omega$) MT2(+), G(+); MT2(+), G(-); MT2(-), G(-) MT2(-), G(+); G(+) "A" Suffix Only	I_{GT}	—	—	5 10	mA
Gate Trigger Voltage (Continuous dc) ($V_D = 12 \text{ V}$, $R_L = 100 \Omega$) MT2(+), G(+); MT2(+), G(-); MT2(-), G(-) MT2(-), G(+); G(+) "A" Suffix Only ($V_D = \text{Rated } V_{\text{DRM}}$, $T_C = 110^\circ\text{C}$, $R_L = 10 \text{ k}$) MT2(+), G(+); MT2(+), G(-); MT2(-), G(-) MT2(-), G(+); G(+) "A" Suffix Only	V_{GT}	— — 0.2 0.2	— — — —	2 2.5 — —	Volts
Holding Current ($V_D = 12 \text{ Vdc}$, $I_{\text{TM}} = 200 \text{ mA}$, Gate Open)	I_H	—	—	15	mA
Gate-Controlled Turn-On Time ($V_D = \text{Rated } V_{\text{DRM}}$, $I_{\text{TM}} = 16 \text{ A Peak}$, $I_G = 30 \text{ mA}$)	t_{gt}	—	1.5	—	μs
Critical Rate of Rise of Off-State Voltage ($V_D = \text{Rated } V_{\text{DRM}}$, Exponential Waveform, $T_C = 110^\circ\text{C}$)	dv/dt	—	25	—	$\text{V}/\mu\text{s}$
Critical Rate of Rise of Commutation Voltage ($V_D = \text{Rated } V_{\text{DRM}}$, $I_{\text{TM}} = 11.3 \text{ A}$, Commutating di/dt = 4.1 A/ms, Gate Unenergized, $T_C = 80^\circ\text{C}$)	$dv/dt[\text{cl}]$	—	5	—	$\text{V}/\mu\text{s}$

FIGURE 1 — RMS CURRENT DERATING

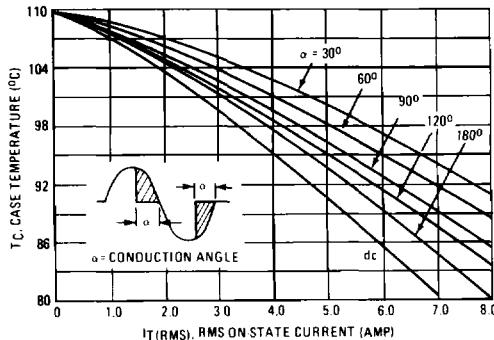


FIGURE 2 — ON-STATE POWER DISSIPATION

